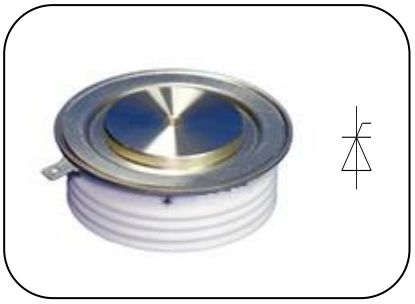
Features

- Excellent dynamic characteristics
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Design for inverter supply application

品名： FH350TN	
$I_{T(AV)}$	**350A**
V_{DRM}	**4000V~4500V**
V_{RRM}	**1000V~3000V**
t_q	**50~120μs**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(°C)	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T_C=55°C	125			350	A
V_{DRM}	Repetitive peak off-state voltage	tp=10ms		125	4000		4500	V
V_{RRM}	Repetitive peak reverse voltage			125	1000		3000	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}		125			60	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}		125			5.0	kA
I^2t	I^2t for fusing coordination						125	A^2s*10^3
V_{TO}	Threshold voltage			125			1.48	V
r_T	On-state slope resistance						2.00	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=1000A, F=15kN	50≤tq≤60	25			3.60	V
			61≤tq≤120				2.80	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM}		125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V_{DM}= 67%V_{DRM} to 1000A, Gate pulse t_r ≤0.5μs I_{GM}=1.5A		125			1200	A/μs
Q_{rr}	Recovery charge	I_{TM}=1000A, tp=4000μs, di/dt=-5A/μs, V_R=100V		125		350		μC
tq	Circuit commutated turn-off time	I_{TM}=1000A, tp=4000μs, V_R=100V dv/dt=30V/μs, di/dt=-5A/μs		125	50		120	μs
I_{GT}	Gate trigger current	V_A=12V, I_A=1A		25	40		250	mA
V_{GT}	Gate trigger voltage				0.9		2.5	V
I_H	Holding current				20		400	mA
I_L	Latching current						500	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	DC, double side cooled Clamping force 15kN					0.035	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.008	
F_m	Mounting force				10		20	kN
T_{vj}	Junction temperature				-40		125	°C
T_{stg}	Stored temperature				-40		140	°C
W_t	Weight					250		g
Outline	P08							

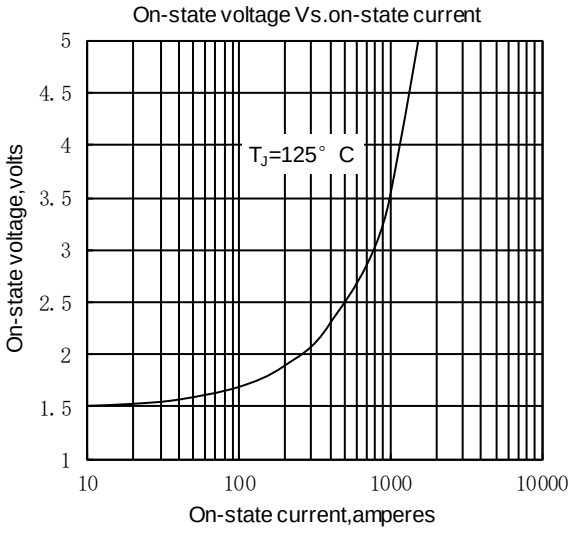


Fig.1

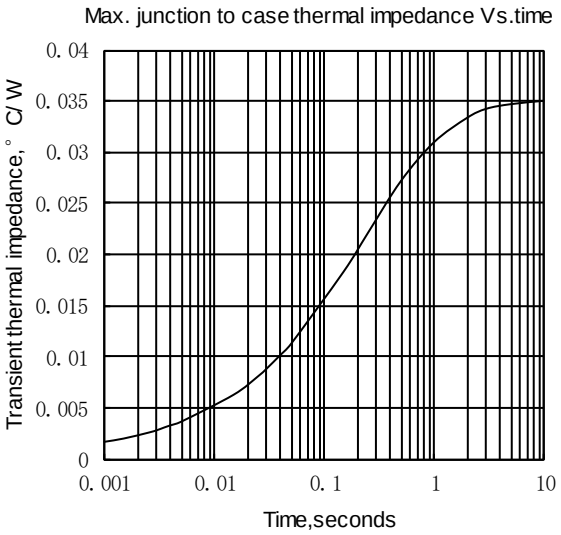


Fig.2

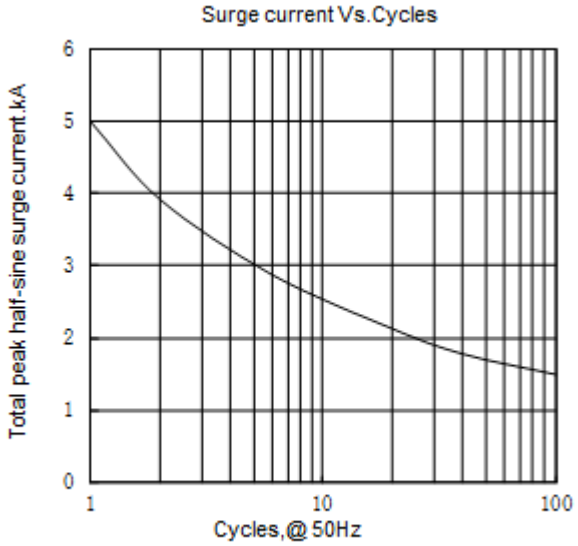


Fig.3

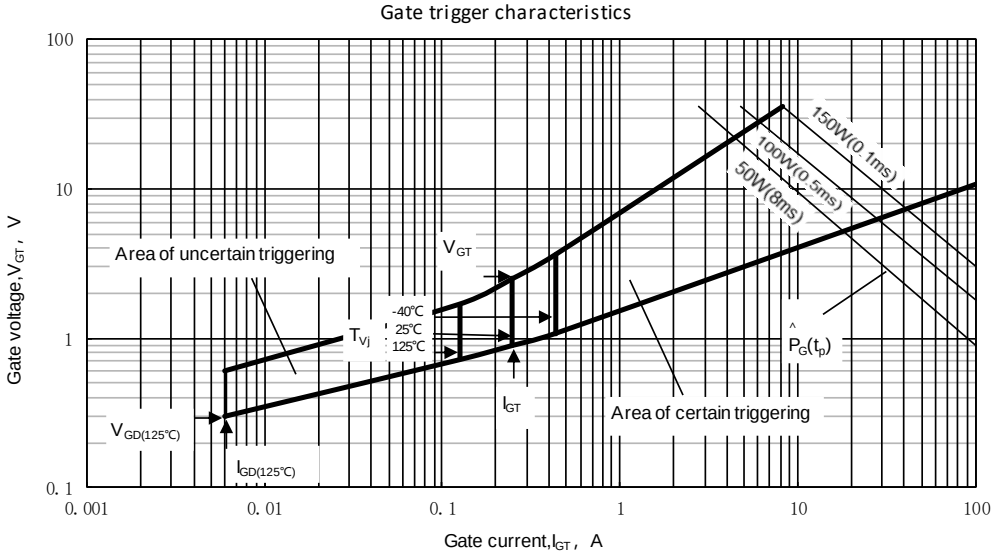


Fig.4